

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

DMP3013SFV-MS

Product specification

Description

The DMP3013SFV-MS uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

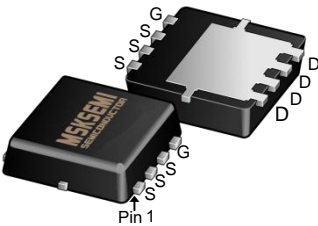
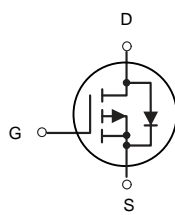

Features

- $V_{DS} = -30V$ $I_D = -55A$
- $R_{DS(ON)} < 11m\Omega$ @ $V_{GS} = 10V$

Application

- Battery protection
- Load switch
- Uninterruptible power supply

Reference News

DFN3X3-8L	P-Channel MOSFET	Marking
		

Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	-30	V
VGS	Gate-Source Voltage	± 20	V
$I_D @ T_c=25^\circ C$	Continuous Drain Current, V_{GS} @ 10V ¹	-55	A
$I_D @ T_c=100^\circ C$	Continuous Drain Current, V_{GS} @ 10V ¹	-23	A
IDM	Pulsed Drain Current ²	-140	A
EAS	Single Pulse Avalanche Energy ³	78.8	mJ
$P_D @ T_c=25^\circ C$	Total Power Dissipation ⁴	21.5	W
TSTG	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	5.8	$^\circ C/W$

Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -30V, V _{GS} = 0V,	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-1.5	-2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note3</small>	V _{GS} =-10V, I _D =-12A	-	8.5	11	mΩ
		V _{GS} =-4.5V, I _D =-8A	-	13	18	
C _{iss}	Input Capacitance	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz	-	2800	-	pF
C _{oss}	Output Capacitance		-	346	-	pF
C _{rss}	Reverse Transfer Capacitance		-	319	-	pF
Q _g	Total Gate Charge		-	30	-	nC
Q _{gs}	Gate-Source Charge	V _{DS} = -15V, I _D = -20A, V _{GS} = -10V	-	5.3	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	7.6	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} = -15V, I _D = -20A, V _{GS} =-10V, R _{GEN} =2.5Ω	-	14	-	ns
t _r	Turn-on Rise Time		-	20	-	ns
t _{d(off)}	Turn-off Delay Time		-	95	-	ns
t _f	Turn-off Fall Time		-	65	-	ns
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-55	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-140	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = -35A	-	-0.8	-1.2	V

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition: T_J= 25°C, V_{DD}= -20V, V_G= -10V, L= 0.5mH, R_G= 25Ω, I_{AS}= -17A
3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Performance Characteristics

Figure 1: Output Characteristics

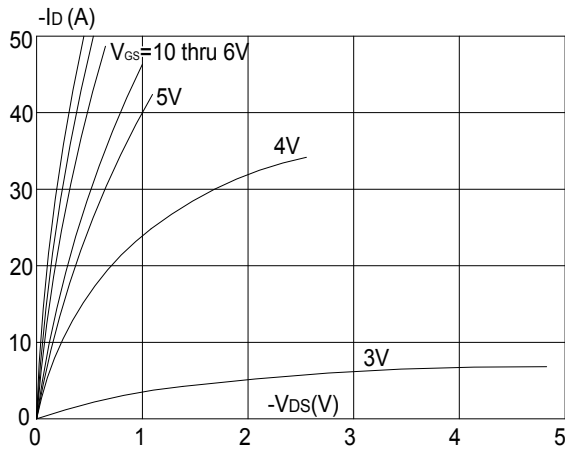


Figure 2: Typical Transfer Characteristics

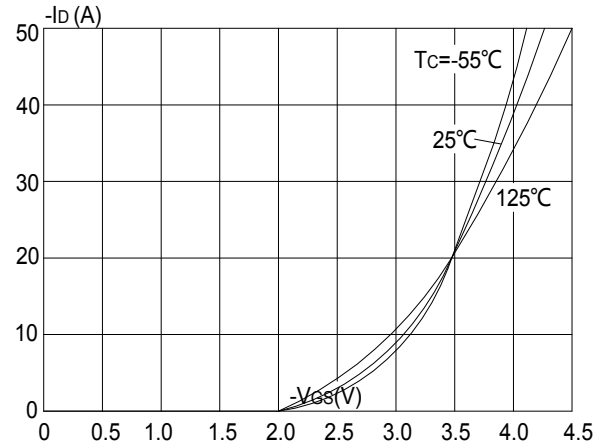


Figure 3: On-resistance vs. Drain Current

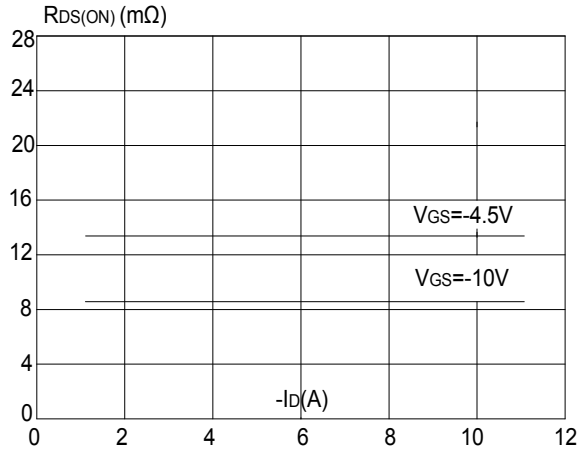


Figure 4: Body Diode Characteristics

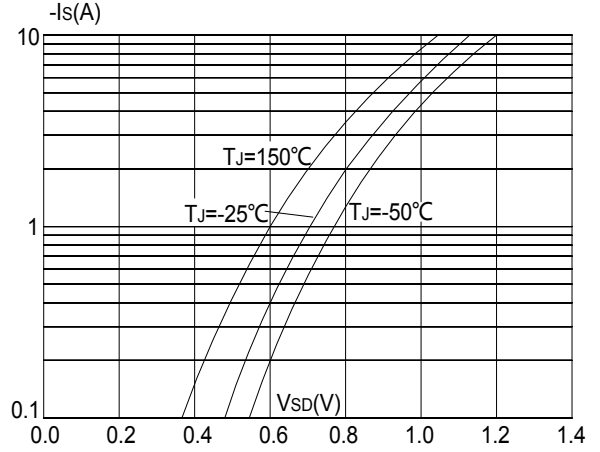


Figure 5: Gate Charge Characteristics

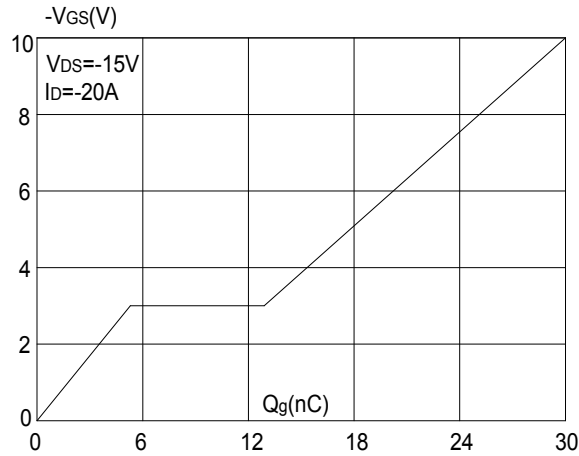


Figure 6: Capacitance Characteristics

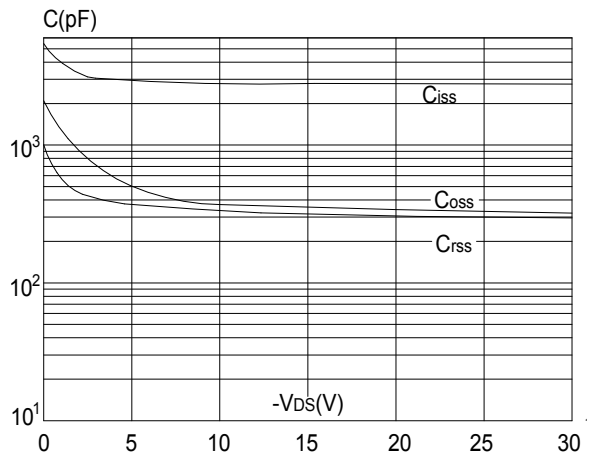


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

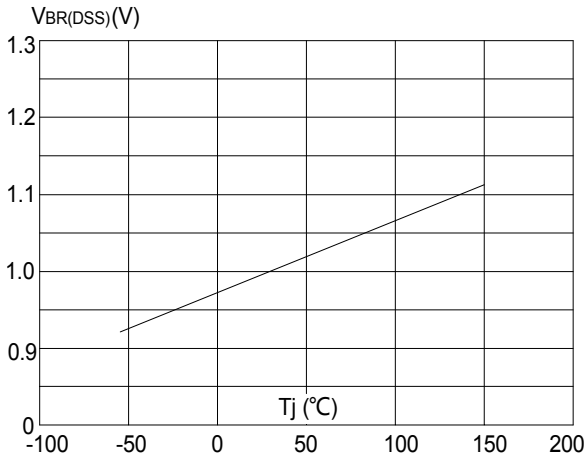


Figure 8: Normalized on Resistance vs. Junction Temperature

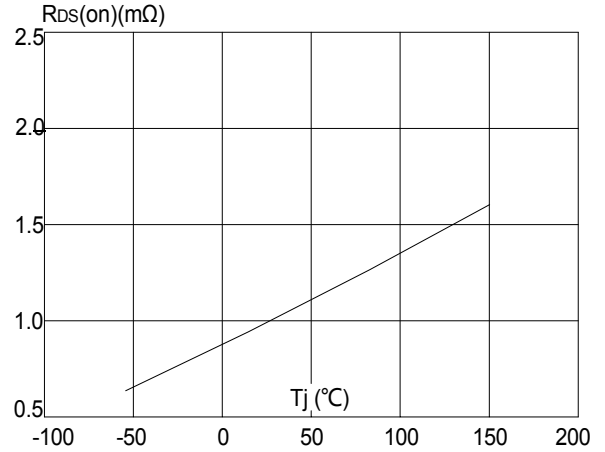


Figure 9: Maximum Safe Operating Area

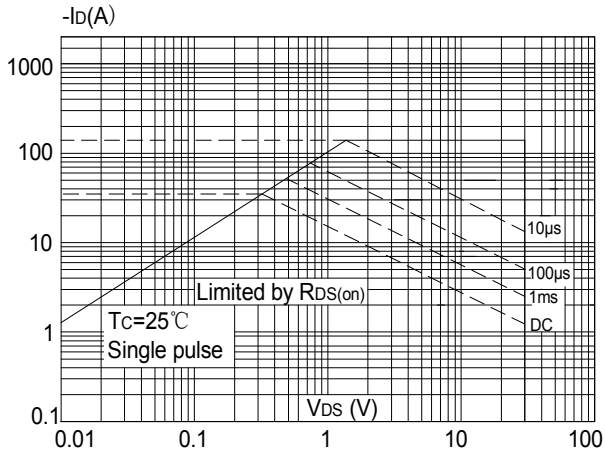


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

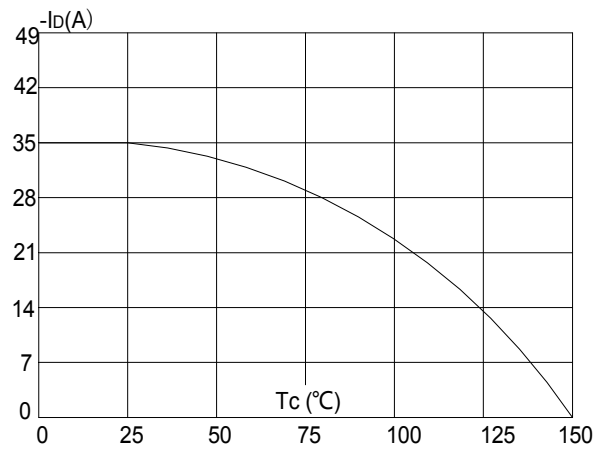
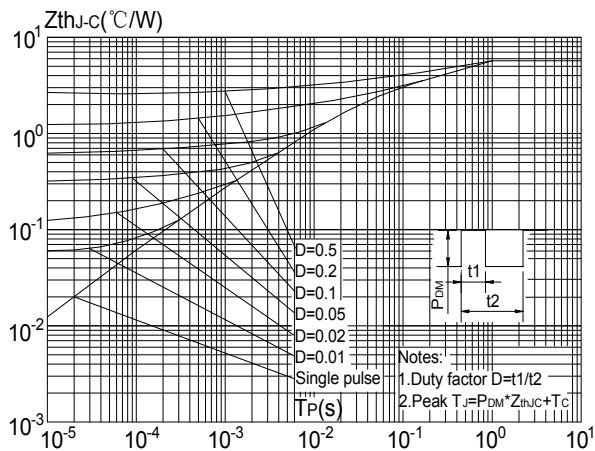
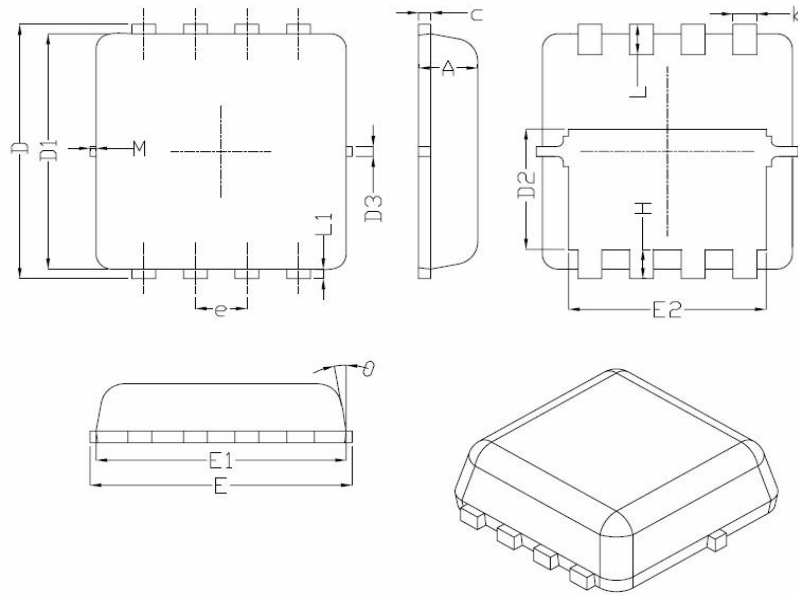


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



DFN3X3-8L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°

REEL SPECIFICATION

P/N	PKG	QTY
DMP3013SFV-MS	DFN3X3-8L	5000

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